## **Cutoff Probe for Process Monitoring**

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In this paper, we present the recent progress of the cutoff probe research for the plasma process monitoring. This paper shows thewhole progress for the cutoff probe including how to start to develop thecutoff probe in the initial period, what idea has been included during the development, how to evolve the probe during ten years, especially for plasma process monitoring. The cutoff probe was made by simple intuition for the cutoff phenomenon of the plasma wave. However, theunexpected complicated S21 spectrum gave big confusion for the cutofffrequency. At that time, just compared the cutoff probe result with the otherprobe result such as Langmuir probe and oscillation probe, the cutoff frequencycould be determined. Later, EM waver simulation supported the validation forthe cutoff frequency determination. Recently, by supposing the circuitmodeling, the physics behind for the cut off probe spectrum (S21) was revealed and the accuracy and the application windowof the probe were established. In addition to them. By cooperating with theaccuracy measurement of the cutoff probe reactance, the e-n collision frequencyas well as the electron density were calculated with good precision. The fastmeasurement cutoff probe "named fourier cutoffprobe" which can applied to therapid change environment of plasma has been also developed. Based on recentdevelopments we also introduce a novel methodology to interpret the probespectrum that eliminates the sheath and collisional effects and enables the useof this precise diagnostic technique in a broad range of practical processing conditions. Recent developed new type of cutoff probe called planar cutoff probe is presented as well.